

CentralTM Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

1N3600
1N4150

SILICON SWITCHING DIODE

JEDEC DO-35 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 1N3600, 1N4150, silicon planar epitaxial diode is characterized by its miniature size, ultra fast switching speed, low capacitance, low leakage, and high conductance. Accordingly, it is ideally suited for applications such as pulse applications, avalanche circuits, core drivers, and for any critical circuit requiring high conductance at power dissipation without sacrificing fast recovery capability. (Both devices have identical electrical and mechanical specifications).

MAXIMUM RATINGS (T_A=25°C)

	SYMBOL		UNIT
Peak Working Inverse Voltage	V _{RWM}	50	V
Average Forward Current	I _O	200	mA
Forward Steady State Current	I _F	400	mA
Recurrent Peak Forward Current	i _f	600	mA
Peak Forward Surge Current (1.0s Pulse)	I _{FSM}	1.0	A
Peak Forward Surge Current (1.0us Pulse)	I _{FSM}	4.0	A
Power Dissipation	P _D	500	mW
Operating and Storage Junction Temperature	T _J , T _{STG}	-65 to +200	°C

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
I _R	V _R =Rated V _{RWM}		100	nA
I _R	V _R =Rated V _{RWM} , T _A =150°C		100	μA
BV _R	I _R =5.0μA	75		V
V _F	I _F =1.0mA	0.54	0.62	V
V _F	I _F =10mA	0.66	0.74	V
V _F	I _F =50mA	0.76	0.86	V
V _F	I _F =100mA	0.82	0.92	V
V _F	I _F =200mA	0.87	1.0	V
C	V _R =0V, f=1.0MHz		2.5	pF
t _{fr}	V _f =1.0V, I _f =200mA, t _r =0.4ns		10	ns
t _{rr}	I _f =I _r =10mA to 200mA, R _L =100Ω		4.0	ns
t _{rr}	I _f =I _r =200mA to 400mA, R _L =100Ω		6.0	ns